### 6/15/2006 1:14:18 PM 6/15/2006 1:53:18 PM

[File 2] INSPEC 1898-2006/Jan W2

[File 6] NTIS 1964-2006/Jan W4

[File 8] Ei Compendex(R) 1970-2006/Jan W4

[File 34] SciSearch(R) Cited Ref Sci 1990-2006/Jan W4

[File 434] SciSearch(R) Cited Ref Sci 1974-1989/Dec

[File 35] Dissertation Abs Online 1861-2006/Jan

[File 65] Inside Conferences 1993-2006/Jan W5

[File 94] JICST-EPlus 1985-2006/Nov W3

[File 99] Wilson Appl. Sci & Tech Abs 1983-2006/Apr

[File 144] Pascal 1973-2006/Jan W2

[File 23] CSA Technology Research Database 1963-2006/Jan

[File 103] Energy SciTec 1974-2006/Jan B1

[File 31] World Surface Coatings Abs 1976-2006/Jan

[File 95] TEME-Technology & Management 1989-2006/Jan W5

[File 56] Computer and Information Systems Abstracts 1966-2006/Jun

[File 57] Electronics & Communications Abstracts 1966-2006/Jun

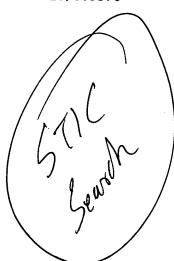
[File 68] Solid State & Superconductivity Abstracts 1966-2006/Jan

[File 60] ANTE: Abstracts in New Tech & Engineer 1966-2006/Jan

[File 293] Engineered Materials Abstracts 1966-2006/Jan

[File 239] Mathsci 1940-2005/Feb

[File 256] TECINFOSOURCE 82-2005/DEC



#### Set Items Description

942858 S LCD? ? OR LIQUID()CRYSTAL()(DISPLAY????? OR PANEL????? OR MATRI????? OR SCREEN? ?) OR (FLAT OR PASSIVE OR ACTIVE)(2N)(DISPLAY???? OR PANEL???? OR MATRI???? OR SCREEN? ?) OR LIQUID(2N)CRYSTAL OR LCM OR DISPLAY(2N)(MEANS OR DEVICE? ? OR APPARATUS OR APPT? ?) OR FED? ? OR FIELD()(EMIS????? OR EMIT?????)()(DISPLAY????? OR PANEL????? OR MATRI??????? OR SCREEN? ?) OR PDP? ? OR PLASMA(2N)(DISPLAY???? OR PANEL????? OR MATRI????? OR SCREEN? ?) OR THIN()FILM()TRANSISTOR OR FET? ? OR FIELD()EFFECT()TRANSISTOR? ?

**S2** 40108455 S INSPECT????? OR DETERMIN??????? OR MEASUR????????? OR TEST?????? OR ESTIMAT????? OR ANALY????????? OR MONITOR???????? OR CHECK???? OR ASSESS?????????? OR EXAM??????????

S3 275756 S (SIGNAL???? OR INFORMATION OR DATA OR PHAS??????? OR INFO)(3N)(WIRE? ? OR WIRING OR FLEX???? OR LINE? ? OR TRAC??????)

**54** 45936 S ESD? ? OR GESD? ? OR DESD? ? OR ELECTROSTATIC?????(3N) (DISCHARG????? OR PROTECT????? OR DAMAG?????? OR DEFECT????? OR DISTURB?????? OR FLAW? ?) OR ELECTROSTATIC????(3N) (DEVICE? ? OR APPARATUS OR APPT? ? OR MEANS)

S5 211158 S (CONDUCT???????? OR SHORT???) (3N) (BAR? ? OR ROD? ? OR ELECTROD???? OR ANOD???? OR CATHOD????? OR PROB??????? OR PLATE? ? OR LINE? ? OR TRAC?????) OR GSL? ? OR DSL? ? OR GATE()SHORT????()LINE? ?

**S6** 215167 S (CURRENT OR VOLT?????)(3N)(PATH????? OR COURS????? OR LINE? ? OR DIRECT????? OR TRACK?????? OR TRAIL???? OR ROUT?????)

\$3 8363786 S DEFECT?????? OR IMPERFECT??????? OR STRESS?????? OR BREAK?????? OR FLAW??? OR CRACK???? OR DETERIORAT??? OR DEGRAD??????? OR DECAY?????? OR DECLIN???? OR DEGENERAT????

**58** 237197 S (INDIVIDUAL?????? OR SINGL????? OR RESPECTIVE??????? OR SINGULAR????? OR SPECIF?????? OR PARTICULAR????? OR SEPAR??????) (3N) (SHORT???? OR SHORT()CIRCUIT?????? OR END? ? OR POINT? ? OR OPEN()CIRCUIT?????)

 S9
 0
 S
 S1
 AND
 S2
 AND
 S3
 AND
 S4
 AND
 S5
 AND
 S6
 AND
 S7
 AND
 S8

 S10
 0
 S
 S1
 AND
 S2
 AND
 S4
 AND
 S5
 AND
 S6
 AND
 S7

 S11
 293
 S
 S1
 AND
 S2
 AND
 S7
 AND
 S4

**S12** 2 S S11 AND S5

\$13 1 RD (unique items)

**S14** 1 S S11 AND S8

**S15** 3 S S11 AND S3

S16 3 RD (unique items)

**S17** 5 S S11 AND S6

\$18 5 RD (unique items)

### 6/15/2006 1:14:18 PM 6/15/2006 1:53:18 PM

```
3 S S18 AND PY<=2003
             0 S S1 AND S4 AND S5 AND S8
12 S S1 AND S4 AND S5
11 RD (unique items)
S20
S21
S22
S23
             11 S S22 AND PY<=2003
             0 S S1 AND S3 AND S4 AND S5
0 S S1 AND S3 AND S5 AND S8
S24
S25
S26
             19 S S1 AND S3 AND S5 AND S7
             9 RD (unique items)
S27
                   S S27 AND PY<=2003
S28
              8
             1 S S14 NOT S13
S29
             3 S S16 NOT (S13 OR S14)
3 S S19 NOT (S13 OR S14 OR S16)
10 S S23 NOT (S13 OR S14 OR S16 OR S19)
S30
S31
S32
             8 S S28 NOT (S13 OR S14 OR S16 OR S19 OR S23)
S33
```

30/9/1 (Item 1 from file: 6) **Links** 

Fulltext available through: Check for PDF Download Availability and Purchase

**NTIS** 

(c) 2006 NTIS, Intl Cpyrght All Rights Res. All rights reserved. 1340957 NTIS Accession Number:

NTN87-1157

Transient Protection of Electronic Circuits: Report reviews protection from different forms of electromagnetic pulses

(NTIS Tech Note)

Department of the Air Force, Washington, DC.

Corporate Source Codes: 000260000

Dec 87 1p

Language: English

Journal Announcement: GRAI8804

FOR ADDITIONAL INFORMATION: Detailed information about the technology described may be obtained by

ordering the NTIS report order number: AD-A178945/2/NAC, price code: A10.

NTIS Prices: Not available NTIS
Country of Publication: United States

This citation summarizes a one-page announcement of technology available for utilization. Because many modern semiconductor devices (small signal transistors, integrated circuits) can be damaged by potential differences that exceed about 20 to 40 V, the survivability of modern electronics is limited. Modern electronic technology has tended to produce smaller and faster semiconductor devices, particularly high-speed digital logic, microprocessors, metal-oxide-semiconductor (MOS) memories for computers, and GaAs field effect transistors (FETs) for microwave use. This progress has led to an increased vulnerability of modern circuits to damage by transient overvoltages, because of the inability of small components to conduct large currents. Electromagnetic pulses from nuclear weapons, lightning, and electrostatic discharge are three examples of such electrical overstress. Such overstress can cause failure, permanent degradation, or temporary malfunction (upset) of electronic devices and systems. This problem and general solutions have been reviewed in a technical report. Nonlinear components and circuits for protection for electrical overstress are discussed in detail, emphasizing spark gaps, metal oxide varistors, and avalanche diodes. However, other components, such as semiconductor diodes, thyristors, resistors, inductors, and optoisolators are also discussed. Applications of these nonlinear components are discussed in the context of signal lines, AC power lines, and DC power supplies. A final chapter discusses specific upset protection circuits.

**Descriptors:** \*Circuit protection; \*Electromagnetic pulses **Identifiers:** \*Transient radiation effects; NTISNTND

Section Headings: 49B (Electrotechnology--Circuits)

32/9/8 (Item 2 from file: 95) <u>Links</u>
TEME-Technology & Management
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01082618 E97031037048
Interconnects for device ESD protection

(Kurzschlussverbindung zum Schutz von Bauelementen vor elektrostatischer Entladung)

Jarrett, T; Unger, B

Guidant St. Paul, USA; CRO-BAR Monmouth Beach, USA

Electrical Overstress/Electrostatic Discharge Symp. Proc. 1996, Orlando, USA, Sep 10-12, 1996, 1996

Document type: Conference paper Language: English

Record type: Abstract ISBN: 1-878303-69-4

### **Abstract:**

A conductive spring loaded shorting bar on the leads of a TO-220 MOSFET was found to protect it from ESD failures. The MOSFET is used in a medically implantable device where quality and reliability is essential. Pre-production samples revealed significant ESD failures, thought to be associated with a mechanical shearing operation. Analysis suggests CDM failures, since testing revealed a low CDM threshold. A custom designed removable shorting interconnect raised all ESD thresholds by at least an order of magnitude. No failures have occured in thousands of devices used since the interconnect was incorporated.

Descriptors: CARDIAC PACEMAKERS; ELECTROSTATIC CHARGING; METAL OXIDE SEMICONDUCTOR FET; SHORT CIRCUIT; ELECTRIC CONTACTS; ELECTROSTATIC DISCHARGE;

PRODUCT QUALITY

Identifiers: Herzschrittmacher; elektrostatischer MOSFET-Entladungsschutz

33/9/2 (Item 2 from file: 2) **Links** 

**INSPEC** 

(c) 2006 Institution of Electrical Engineers. All rights reserved. 06658128 INSPEC Abstract Number: B9709-2240-014 Title: Adhesive and conductive adhesive flip chip bonding

Author Zenner, R.L.D.; Connell, G.; Gerber, J.A. Author Affiliation: 3M Co., St. Paul, MN, USA

Conference Title: Proceedings. 3rd International Symposium on Advanced Packaging Materials Processes,

Properties and Interfaces (Cat. No.97TH8263) p. 117-19

Publisher: IEEE, New York, NY, USA

**Publication Date:** 1997 **Country of Publication:** USA viii+183 pp. **ISBN:** 0 7803 3818 9 **Material Identity Number:** XX97-00693

Conference Title: Proceedings 3rd International Symposium on Advanced Packaging Materials Processes,

Properties and Interfaces

Conference Sponsor: Int. Microelectron. & Packaging Soc. (IMAPS); IEEE Components, Packaging, & Manuf.

Technol. Soc.; Georgia Inst. Technol., Pakcaging Res. Center (PRC)

Conference Date: 9-12 March 1997 Conference Location: Braselton, GA, USA

Language: English Document Type: Conference Paper (PA)

Treatment: Practical (P); Experimental (X)

Abstract: Over the past decade the use of adhesives for electronic interconnect has been driven by the explosive growth of flat panel liquid crystal displays (LCD). Developed and used primarily by Japanese manufacturers of consumer products, particle-loaded adhesive films fulfilled a need in LCDs that could not be met by solder reflow: low temperature, high line density (to 50 mu m pitch) electrical interconnect to indium tin oxide (ITO) traces on glass. Adhesives may also be used for flip-chip assembly. The advantages of flip-chip attach technology are the same for solder or adhesive technology: footprint reduction, low interconnect resistance, short signal line length, and elimination of single-chip packaging costs. Lower parasitics decrease rise times and decrease power requirements. To prevent differential thermal expansion induced solder fatigue, flip-chip attachment using solder reflow requires the use of an underfill adhesive applied in a separate time-consuming process. Adhesive films described in this paper inherently provide an underfill, serve as environmental protection for the chip face, as well as make a solderless electrical connection. Performance results for fine pitch chips have shown stable interconnect resistance below 10 m Omega for bumped chip applications and approximately 100 m Omega with unbumped chip test vehicles. The adhesive flip-chip bonding process and environmental stress results will be presented in this paper. (2 Refs)

Subfile: B

**Descriptors:** adhesion; fine-pitch technology; flip-chip devices

Identifiers: adhesive; flip chip bonding; conductive adhesive; flat panel liquid crystal display; particle-loaded adhesive; fine pitch technology; underfill adhesive film; electric interconnect resistance; environmental stress; 50

micron; 10 mohm; 100 mohm

Class Codes: B2240 (Microassembly techniques)

Numerical Indexing: size 5.0E-05 m; resistance 1.0E-02 ohm; resistance 1.0E-01 ohm

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6/15/2006 2:15:20 PM 6/15/2006 2:49:01 PM

- [File 344] Chinese Patents Abs Jan 1985-2006/Jan [File 347] JAPIO Nov 1976-2005/Sep(Updated 060103) [File 350] Derwent WPIX 1963-2006/UD,UM &UP=200607
- [File 371] French Patents 1961-2002/BOPI 200209
- Set Items Description
- \$1 1235628 S LCD? ? OR LIQUID()CRYSTAL()(DISPLAY????? OR PANEL????? OR MATRI????? OR SCREEN? ?) OR (FLAT OR PASSIVE OR ACTIVE)(2N)(DISPLAY???? OR PANEL???? OR MATRI???? OR SCREEN? ?) OR LIQUID(2N)CRYSTAL OR LCM OR DISPLAY(2N)(MEANS OR DEVICE? ? OR APPARATUS OR APPT? ?) OR FED? ? OR FIELD()(EMIS????? OR EMIT?????)()(DISPLAY????? OR PANEL????? OR MATRI??????? OR SCREEN? ?) OR PDP? ? OR PLASMA(2N)(DISPLAY???? OR PANEL????? OR MATRI???? OR SCREEN? ?) OR THIN()FILM()TRANSISTOR OR FET? ? OR FIELD()EFFECT()TRANSISTOR? ?
- **S2** 4244110 S INSPECT????? OR DETERMIN??????? OR MEASUR????????? OR TEST?????? OR ESTIMAT????? OR ANALY????????? OR MONITOR??????? OR CHECK???? OR ASSESS????????? OR EXAM?????????
- S3 286788 S (SIGNAL???? OR INFORMATION OR DATA OR PHAS??????? OR INFO)(3N)(WIRE? ? OR WIRING OR FLEX???? OR LINE? ? OR TRAC??????)
- S4 29893 S ESD? ? OR GESD? ? OR DESD? ? OR ELECTROSTATIC?????(3N) (DISCHARG????? OR PROTECT????? OR DAMAG?????? OR DEFECT????? OR DISTURB?????? OR FLAW? ?) OR ELECTROSTATIC????(3N) (DEVICE? ? OR APPARATUS OR APPT? ? OR MEANS)
- S5 168471 S (CONDUCT???????? OR SHORT???) (3N) (BAR? ? OR ROD? ? OR ELECTROD???? OR ANOD???? OR CATHOD???? OR PROB??????? OR PLATE? ? OR LINE? ? OR TRAC?????) OR GSL? ? OR DSL? ? OR GATE()SHORT????()LINE? ?
- **56** 139035 S (CURRENT OR VOLT?????)(3N)(PATH????? OR COURS????? OR LINE? ? OR DIRECT????? OR TRACK?????? OR TRAIL???? OR ROUT????)
- S7 1412819 S DEFECT?????? OR IMPERFECT??????? OR STRESS?????? OR BREAK?????? OR FLAW??? OR CRACK???? OR DETERIORAT??? OR DEGRAD??????? OR DECAY?????? OR DECLIN???? OR DEGENERAT????
- **S8** 162300 S (INDIVIDUAL?????? OR SINGL????? OR RESPECTIVE??????? OR SINGULAR????? OR SPECIF?????? OR PARTICULAR????? OR SEPAR??????) (3N) (SHORT???? OR SHORT()CIRCUIT?????? OR END? ? OR POINT? ? OR OPEN()CIRCUIT?????)

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S IC=(G01R-031/00 OR G02F-001/13)
92
        88892
S10
                S MC=(S01-G04C OR S01-G09 OR S02-J04A3A OR U11-F01D3 OR U14-K01A8)
                S S1 AND S2 AND S3 AND S4 AND S5 AND S6 AND S7
S11
            0
S12
                S S1 AND S2 AND S7 AND S4 AND S5
S13
            5
                S S12 AND PY<=2003
S14
            1
                S S1 AND S2 AND S3 AND S4 AND S8
S15
           23
                S S1 AND S4 AND S5 AND S7
816
                S S15 AND PY<=2003
           18
S17
                S S1 AND S2 AND S3 AND S4 AND S6
            2
S18
                S S16 AND S9
            1
S19
            0
                S S16 AND S10
S20
                S S1 AND S2 AND S3 AND S4 AND S5 AND S6
                S S1 AND S2 AND S7
        19925
S21
S22
         1875
                S S21 AND S9
S23
          359
                S S22 AND S10
S24
           75
                S S21 AND S4
S25
            7
                S S24 AND S9
S26
            1
                S S24 AND S10
S27
            4
                S S3 AND S4 AND S5 AND S8
S28
            4
                S S27 AND PY<=2003
S29
            5
                S S25 AND PY<=2003
                S S17 NOT S14
S30
            2
S31
            1
                S S18 NOT (S14 OR S17)
                S S26 NOT (S14 OR S17 OR S18)
S32
            1
                S S28 NOT (S14 OR S17 OR S18 OR S26)
S33
                S S29 NOT (S14 OR S17 OR S18 OR S26 OR S28)
834
S35
            4
                S S13 NOT (S14 OR S17 OR S18 OR S26 OR S28 OR S29)
                S S16 NOT (S13 OR S14 OR S17 OR S18 OR S26 OR S28 OR S29)
S36
           13
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14/9/1 (Item 1 from file: 347) **Links** 

**JAPIO** 

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04994649 \*\*Image available\*\*

### THIN FILM TRANSISTOR ARRAY AND ITS INSPECTION METHOD

**Pub. No.:** 07-287249 [JP 7287249 A] **Published:** October 31, 1995 (19951031)

**Inventor: NISHIKI TAMAHIKO** 

**OGURA SHIGEKI** 

YOSHIZAWA YOSHIYO

Applicant: OKI ELECTRIC IND CO LTD [000029] (A Japanese Company or Corporation), JP (Japan)

Application No.: 06-080081 [JP 9480081]

Filed: April 19, 1994 (19940419)

International Class: [6] G02F-001/136; G02F-001/1343; H01L-021/66; H01L-029/786

JAPIO Class: 29.2 (PRECISION INSTRUMENTS -- Optical Equipment); 42.2 (ELECTRONICS -- Solid State

Components); 46.2 (INSTRUMENTATION -- Testing)

JAPIO Keyword: R011 (LIQUID CRYSTALS); R096 (ELECTRONIC MATERIALS -- Glass Conductors)

### **ABSTRACT**

PURPOSE: To provide the **TFT** array with a short-circuiting wire and its **inspection** method which enables the **inspection** of a short circuit between layers by simple conduction **inspection** after the **TFT** array is completed.

CONSTITUTION: The **thin film transistor** array, which is provided with thin film transistors at respective intersection parts of plural address **lines** and plural **data lines** arranged crossing each other and has a display area having an auxiliary capacity line connected to the thin film transistors and also has a 1st short-circuiting wire arranged outside the display area through an **electrostatic protection** element, is equipped with a short-circuiting wire 31 for the **data lines** 12 which is arranged outside the 1st short-circuiting wire 30, a short-circuiting wire 31 for the address lines 11 which is arranged outside the 1st short-circuiting wire 30, and a short-circuiting wire 31 for the auxiliary capacity line 13 connected by the same metallic layer as the short-circuiting wire 31 for the address lines 11; and a discharging stylus is provided as the **electrostatic protecting means** 40 at the **separation** part between the **short-circuiting wire** 32 for the **data lines** 12, and the short-circuiting wire 31 for the address lines 11 and short-circuiting wire 31 for the auxiliary capacity line 13.

31/9/1 (Item 1 from file: 347) **Links** 

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05985142 \*\*Image available\*\*

## MANUFACTURE OF LIQUID CRYSTAL DISPLAY DEVICE

**Pub. No.:** 10-268242 [JP 10268242 A] **Published:** October 09, 1998 (**19981009**)

**Inventor: YAMANAKA HIDEO** 

Applicant: SONY CORP [000218] (A Japanese Company or Corporation), JP (Japan)

**Application No.:** 09-074744 [JP 9774744]

Filed: March 27, 1997 (19970327) International Class: [6] G02F-001/13

JAPIO Class: 29.2 (PRECISION INSTRUMENTS -- Optical Equipment)

JAPIO Keyword: R011 (LIQUID CRYSTALS)

### **ABSTRACT**

PROBLEM TO BE SOLVED: To provide a manufacturing method of a liquid crystal display device preventing an electrostatic damage, preventing metallic dust caused by a probe test as it is from sticking on a liquid crystal drive substrate and thus, preventing deterioration in yield and quality caused by the sticking of the metallic dust.

SOLUTION: A liquid crystal drive substrate 1 forming a conductive short line short-circuiting all electrode pads in at least a scribed area is provided, and an oriented film 3 is formed on its inner surface, and succeedingly, rubbing processing of the oriented film 3 is performed. Then, the liquid crystal drive substrate 1 is mounted on a dicing sheet 4, and taper shaving processing of a V groove 6 in the scribe area of the liquid crystal drive substrate 1 in its state is performed, and the short line in the scribe area is removed, and the short circuit between the electrode pads is released. Then, the liquid crystal drive substrate 1 in the state as it is mounted on the dicing sheet 4 is probe tested. Thereafter, taper shaving process parts are full-cut diced.

33/9/2 (Item 1 from file: 350) **Links** 

Derwent WPIX

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015238768 \*\*Image available\*\* WPI Acc No: 2003-299694/**200329** 

XRPX Acc No: N03-238455

Electrostatic discharge protection

circuit for thin film transistor liquid crystal display, uses ESD protection units to connect gate shorting line to data shorting line and to connect data shorting line to common electrode

Patent Assignee: LG PHILIPS LCD CO LTD (GLDS ); KIM Y (KIMY-I); LEE H (LEEH-I)

Inventor: KIM Y; LEE H; KIM Y G; LEE H G

Number of Countries: 006 Number of Patents: 008

Patent Family:

Patent No		Kind	Date	Applicat No		Kind	Date	Week	
US	20030020845	A1	20030130	U	S 2002180979	Α	20020627	200329	В
DE	10228517	A1	20030306	DE	10228517	A	20020626	200329	
JΡ	2003107528	Α	20030409	JΡ	2002190048	Α	20020628	200333	
KR	2003005797	Α	20030123	KR	200141251	Α	20010710	200334	
CN	1396656	Α	20030212	CN	2002140347	Α	20020628	200335	
KR	386849	В	20030609	KR	200141251	Α	20010710	200367	
TW	575766	Α	20040211	TW	2002113993	A	20020626	200454	
US	6791632	B2	20040914	US	2002180979	Α	20020627	200460	

Abstract (Basic): US 20030020845 A1

NOVELTY - An electrostatic discharge (ESD)

protection unit that connects gate shorting

line to data shorting line and another

ESD protection unit that directly connects the data shorting line to a common electrode (ITO), are provided along with ESD protection units for connecting respective gate lines to gate shorting line and data lines to data shorting line,

respectively.

DETAILED DESCRIPTION - An INDEPENDENT CLAIM is also included for method of protecting liquid crystal display **device** from **electrostatic discharge**.

USE - For electrostatic discharge (ESD) rotection of thin film transistors liquid crystal d

protection of thin film transistors liquid crystal display
(TFT-LCD).

ADVANTAGE - Distributes more stable and efficient dispersion of static electric charges into and from the **data lines**.

DESCRIPTION OF DRAWING(S) - The figure shows a schematic circuit diagram of the **electrostatic discharge protection** circuit.

pp; 10 DwgNo 4/6

34/9/4 (Item 1 from file: 350) Links Derwent WPIX (c) 2006 The Thomson Corp. All rights reserved. 013148035 \*\*Image available\*\* WPI Acc No: 2000-319907/200028 Related WPI Acc No: 2004-798418 XRPX Acc No: N00-240117 Semiconductor device for liquid crystal panel with thin film transistors and photoelectric conversion apparatus has common electrode bias line, several gate lines and several transfer lines electrically connected Patent Assignee: CANON KK (CANO ); KAIFU N (KAIF-I); MOCHIZUKI C (MOCH-I); WATANABE M (WATA-I) Inventor: KAIBU K; MOCHITSUKI T; WATANABE S; KAIFU N; MOCHIZUKI C; WATANABE M Number of Countries: 028 Number of Patents: 009 Patent Family: Patent No Date Kind Applicat No Kind Date Week EP 993038 A1 20000412 EP 99306846 19990827 Α 200028 JP 2000148044 Α 20000526 JP 99235770 Α 19990823 200033 CN 1254187 Α 20000524 CN 99118343 19990831 Α 200043 US 20030111664 A1 20030619 US 99384424 19990827 Α 200341 US 2002305981 20021129 Α US 6586769 В1 20030701 US 99384424 19990827 Α 200345 US 20050051779 20050310 A1 US 99384424 Α 19990827 200519 US 2002305981 20021129 Α US 2004969875 A 20041022 US 6909116 B2 20050621 US 99384424 19990827 Α 200543 US 2002305981 Α 20021129 CN 1144292 С 20040331 CN 99118343 19990831 200610 Α US 20060087577 A1 20060427 US 99384424 Α 19990827 200629 US 2002305981 20021129 Α US 2004969875 Α 20041022 US 2005297414 Α 20051209 Priority Applications (No Type Date): JP 99235770 A 19990823; JP 98246151 A 19980831 Patent Details: Patent No Kind Lan Pg Main IPC Filing Notes EP 993038 A1 E 21 H01L-021/84 Designated States (Regional): AL AT BE CH CY DE DK ES FI FR GB GR IE IT LI LT LU LV MC MK NL PT RO SE SI JP 2000148044 A 12 G09F-009/30 CN 1254187 Α H01L-027/10 US 20030111664 A1 G02F-001/1343 Div ex application US 99384424 US 6586769 В1 H01L-029/04 US 20050051779 A1 H01L-029/04

Div ex application US 99384424 Div ex application US 2002305981

Div ex patent US 6586769

US 6909116 B2 H01L-029/04 Div ex application US 99384424 Div ex patent US 6586769

CN 1144292 C H01L-027/10 US 20060087577 A1 G02F-001/13

Div ex application US 99384424 Div ex application US 2002305981 Div ex application US 2004969875 Div ex patent US 6586769 Div ex patent US 6909116

Abstract (Basic): EP 993038 A1

NOVELTY - A gate of each of the number of thin film transistors is connected to a corresponding one of a number of gate lines. The other of the source and the drain of each of the number of thin film transistors are connected to a corresponding transfer line and common electrode bias line. The gate lines and the transfer lines are electrically connected.

DETAILED DESCRIPTION - INDEPENDENT CLAIMS are also included for:

- (a) a substrate carrying a matrix array of rows and columns of switching elements such as thin film transistors;
- (b) an array for **liquid crystal display** or image sensing apparatus.

USE - For a liquid crystal panel with TFTs and a photoelectric conversion apparatus.

ADVANTAGE - Can effectively prevent **electrostatic defects** (**ESD**) during manufacture processes and improve a
manufacture yield. Can maintain the effects of preventing **ESD**until the panel is finally mounted on an apparatus, by electrically connecting wiring lines by resistors. A number of thin film transistors and associated wiring lines are formed on a substrate, in which the wiring lines are disposed vertically and horizontally crossing each other, the wiring lines are electrically insulated at each cross point

DESCRIPTION OF DRAWING(S) - The drawing is a simplified **example** of a semiconductor device of this invention.

pp; 21 DwgNo 1/11

Title Terms: SEMICONDUCTOR; DEVICE; LIQUID; CRYSTAL; PANEL; THIN; FILM; TRANSISTOR; PHOTOELECTRIC; CONVERT; APPARATUS; COMMON; ELECTRODE; BIAS; LINE; GATE; LINE; TRANSFER; LINE; ELECTRIC; CONNECT

Derwent Class: P81; U13; U14

International Patent Class (Main): G02F-001/13; G02F-001/1343;
 G02F-001/136; G09F-009/30; H01L-021/84; H01L-027/10; H01L-029/04
International Patent Class (Additional): G02F-001/133; G02F-001/1365;

H01L-021/822; H01L-021/86; H01L-023/48; H01L-027/02; H01L-027/04;

H01L-029/786; H01L-031/20

File Segment: EPI; EngPI

Manual Codes (EPI/S-X): U13-E01; U14-H01A; U14-K01A1B; U14-K01A2B

35/9/1 (Item 1 from file: 347) **Links** 

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06061333 \*\*Image available\*\*

# ACTIVE MATRIX LIQUID CRYSTAL DISPLAY DEVICE

**Pub. No.:** 11-002839 [JP 11002839 A] **Published:** January 06, 1999 (**19990106**) **Inventor:** HIROSHIMA MINORU

ISODA TAKASHI Applicant: HITACHI LTD

HITACHI DEVICE ENG CO LTD

Application No.: 09-152342 [JP 97152342]

Filed: June 10, 1997 (19970610)

International Class: G02F-001/136; G02F-001/1345; G09F-009/30; H01L-029/786

### **ABSTRACT**

PROBLEM TO BE SOLVED: To provide the active matrix liquid crystal display device which can actualize short-circuit inspection between signal lines through a short bar and is equipped with electrostatic protecting circuit constitution capable of preventing problems of dielectric breakdown caused at an intersection part between the common line and a signal line of an electrostatic protecting circuit.

SOLUTION: Short bars SHde and SHdo of electrostatic protecting circuits of electrically independent even-numbered signal lines (group) D2j and odd-numbered signal lines (group) D2j-1 are coupled by a coupling element part CONEL consisting of a nonlinear element or high-resistance element and thus placed in an electrically connected state from a floating state. Consequently, both the even-numbered and odd-numbered electrostatic protecting circuit systems are held at the same potential and the intersection parts between the signal lines and common line are held at the same potential to prevent dielectric breakdown.

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35/9/3 (Item 1 from file: 350) **Links** 

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010048648 \*\*Image available\*\* WPI Acc No: 1994-316359/**199439** 

XRPX Acc No: N94-248480

Electrostatic discharge protection method for processing active matrix liquid crystal display - using shorting conductor or

bar, at external lead contact areas, to short out or to connect to one another, all row and column contacts on display

Patent Assignee: HONEYWELL INC (HONE )

Inventor: DODD S R

Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No Kind Date Applicat No Kind Date Week
US 5353142 A 19941004 US 9355047 A 19930429 199439 B

Priority Applications (No Type Date): US 9355047 A 19930429

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

US 5353142 A 5 G02F-001/1343

Abstract (Basic): US 5353142 A

The method includes the step of cutting at least one slot on a second surface into a first plane, the slot being approximately perpendicular to the second surface. The slot has a depth that goes through a portion of the first plane and the slot is about from two to four mils from the first surface of the first plane. The slot has a location proximate to the lead contacts in an area between a shorting conductor and a central area of the first plane. The first plane has a peripheral area extending from the slot to the perimeter of the first plane.

The peripheral area is removed from the first plane, after any desired external connection or attachment to the lead contacts at points between the slot and the central area, any fabrication of the display and any installation of any polarizer, by **breaking** off the peripheral area at the location of the slot, thus, removing the shorting conductor from the display.

ADVANTAGE - Allows **shorting bar** to remain in contact with display's external leads through all of processing steps until display **testing** is ready to commence.

Dwg.1a/1

Title Terms: ELECTROSTATIC; DISCHARGE; PROTECT; METHOD; PROCESS; ACTIVE; MATRIX; LIQUID; CRYSTAL; DISPLAY; SHORT; CONDUCTOR; BAR; EXTERNAL; LEAD; CONTACT; AREA; SHORT; CONNECT; ONE; ROW; COLUMN; CONTACT; DISPLAY

Derwent Class: P81; U14

International Patent Class (Main): G02F-001/1343

35/9/4 (Item 2 from file: 350) Links

**Derwent WPIX** 

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009823293 \*\*Image available\*\* WPI Acc No: 1994-103149/**199413** 

XRPX Acc No: N94-080533

Electronic device e.g. LCD mfg. method on insulating substrate with thin film circuit elements and connections - using anti-electrostatic discharge shorting links between connection tracks during mfr., which are later broken by pulse of electric current between linked tracks

Patent Assignee: PHILIPS ELECTRONICS NV (PHIG ); PHILIPS ELECTRONICS UK LTD (PHIG )

Inventor: YOUNG N D

Number of Countries: 006 Number of Patents: 002

Patent Family:

Patent No Kind Date Kind Date Applicat No Week EP 589519 A2 19940330 EP 93202677 Α 19930916 199413 B JP 6224147 Α 19940812 JP 93234959 Α 19930921 199437

Priority Applications (No Type Date): GB 9220220 A 19920924

Cited Patents: No-SR.Pub

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

EP 589519 A2 E 8 G02F-001/136

Designated States (Regional): DE FR GB IT NL

JP 6224147 A 6 H01L-021/265

Abstract (Basic): EP 589519 A

The electronic device mfg. method involves connecting the a group of the device thin film connection tracks to a removable **ESD** path to protect the tracks from **damage** due to **electrostatic discharge**. The removable **ESD** path is conductive thin film links (6) between the separate thin film tracks (4) of the group.

The tracks (4) and their links may be of, for example, aluminium or a metal silicide. The ESD path is removed by applying an electrical pulse (8) between the linked tracks (4) to pass a sufficiently large current as to evaporate and break the thin film links (6) by Joule heating.

USE/ADVANTAGE - E.g. image sensor or data store with switching matrix. Provides **ESD** protection during mfr. e.g. during ion implantation; avoids damage caused by alternative cutting methods e.g. scribing or laser.

Dwg.2/5

Title Terms: ELECTRONIC; DEVICE; LCD; MANUFACTURE; METHOD; INSULATE; SUBSTRATE; THIN; FILM; CIRCUIT; ELEMENT; CONNECT; ANTI; ELECTROSTATIC; DISCHARGE; SHORT; LINK; CONNECT; TRACK; MANUFACTURE; LATE; BREAK;

36/9/2 (Item 2 from file: 347) **Links** 

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06296049 \*\*Image available\*\*

# LIQUID CRYSTAL DISPLAY DEVICE, ITS PRODUCTION AND DETECTING METHOD OF DEFECT

**Pub. No.:** 11-237641 [JP 11237641 A] **Published:** August 31, 1999 (**19990831**)

Inventor: KIM DONG-GYO LEE SANG-KYUNG BUN BINKYO

Applicant: SAMSUNG ELECTRONICS CO LTD Application No.: 10-346844 [JP 98346844]

Filed: December 07, 1998 (19981207)

Priority: 9766154 [KR 66154], KR (Korea) Republic of, December 05, 1997 (19971205)

9849389 [KR 49389], KR (Korea) Republic of, November 18, 1998 (19981118)

International Class: G02F-001/1343; G02F-001/136

### **ABSTRACT**

PROBLEM TO BE SOLVED: To provide a **thin film transistor** substrate having **short bars** which make detection of short circuit fault easy and which are not **damaged** by **electrostatic** charges by arranging plant and second short bars connected to the first and second wirings, and main **short bars** formed outside the first and second short bars.

SOLUTION: First and second auxiliary short bars 410, 420 are formed between a gate short bar 200 and gate pads 110, 120 and parallel to the gate short bar 200. Third to fifth subshort bars 210, 220, 230 are formed between a data short bar 400 and data pads 510, 520 and parallel to the data short bar 400. In this structure, the first and second auxiliary short bars 410, 420 are connected to G1, G3, and G2, G4, respectively. The third to fifth auxiliary short bars 210, 220, 230 are connected to data lines D1 and D4, D2, D3, respectively.

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36/9/3 (Item 3 from file: 347) **Links** 

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05622253 \*\*Image available\*\*

## MANUFACTURING METHOD OF ACTIVE MATRIX DISPLAY DEVICE

**Pub. No.:** 09-237053 [JP 9237053 A] **Published:** September 09, 1997 (**19970909**)

Inventor: SUZUKI KOJI

Applicant: TOSHIBA CORP [000307] (A Japanese Company or Corporation), JP (Japan)

**Application No.:** 09-055219 [JP 9755219]

Filed: March 10, 1997 (19970310)

International Class: [6] G09F-009/30; G02F-001/136; G09F-009/00

JAPIO Class: 44.9 (COMMUNICATION -- Other); 29.2 (PRECISION INSTRUMENTS -- Optical Equipment)

JAPIO Keyword: R004 (PLASMA); R011 (LIQUID CRYSTALS)

#### ABSTRACT

PROBLEM TO BE SOLVED: To fully prevent the device from electrostatic breakage during and after assembling.

SOLUTION: In the manufacturing method of a display device which drives display cells by an active matrix substrate which has plural row lines A, plural column lines crossing these row lines, and switching elements C each at the crossing points between these row lines and column lines, during and after assembling, a short-circuit line GL is laid in the peripheral section of the active matrix substrate. The end section of each of the row lines and the column lines is connected to the short-circuit line GL through a resistor.

36/9/5 (Item 5 from file: 347) Links

**JAPIO** 

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04601883 \*\*Image available\*\*

# LIQUID CRYSTAL DISPLAY DEVICE AND ITS MANUFACTURE

**Pub. No.:** 06-273783 [JP 6273783 A] **Published:** September 30, 1994 (**19940930**)

Inventor: KANEDA YOSHIHIRO

Applicant: CITIZEN WATCH CO LTD [000196] (A Japanese Company or Corporation), JP (Japan)

Application No.: 05-086952 [JP 9386952]

Filed: March 23, 1993 (19930323)

International Class: [5] G02F-001/1343; G02F-001/133; G02F-001/1345 JAPIO Class: 29.2 (PRECISION INSTRUMENTS -- Optical Equipment)

JAPIO Keyword: R011 (LIQUID CRYSTALS)

Journal: Section: P, Section No. 1849, Vol. 18, No. 688, Pg. 162, December 26, 1994 (19941226)

#### **ABSTRACT**

PURPOSE: To prevent an electrode pattern used for display from being **damaged** by **electrostaticity** and also to make it possible to detect a **defective short**-circuit between each **electrode** pattern, as to a method for manufacturing a **liquid crystal display device**.

CONSTITUTION: The electrode pattern 20 used for display is formed on a substrate 10, a common electrode 30 and a connection wire 40 are arranged by use of the same conductive film. The electrostaticity charged on each electrode pattern 20 at the manufacturing process of the **liquid crystal display device** attains the same potential through the common electrode 30, so that the **breakdown** caused by the discharge between the electrode patterns 20 is not generated, and also, the **defective** short-circuit is detected with the resistance value of the connection wire 40.

36/9/12 (Item 5 from file: 350) Links

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004349236

WPI Acc No: 1985-176114/198529

XRPX Acc No: N85-132217

Electrostatic discharge resistive connector system - includes short-circuiting bar to protect

FET from charges introduced when device is plugged in by consumer

Patent Assignee: ANONYMOUS (ANON )

Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No Kind Date Applicat No Kind Date Week RD 254025 A 19850610 198529 B

Priority Applications (No Type Date): RD 85254025 A 19850520

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

RD 254025 A 1

Abstract (Basic): RD 254025 A

A conductive elastomeric shorting bar (12) is provided which short-circuits the terminals of the circuit card until the connector is fully inserted. When it is fully inserted the bar is displaced and no longer provides a short-circuit.

In this way a make-before-break system is provided which protects the **FETs** in the equipment.

Title Terms: ELECTROSTATIC; DISCHARGE; RESISTOR; CONNECT; SYSTEM; SHORT; CIRCUIT; BAR; PROTECT; FET; CHARGE; INTRODUCING; DEVICE; PLUG; CONSUME

Index Terms/Additional Words: PCB

Derwent Class: U11; V04; X25

International Patent Class (Additional): H05F-000/01; H05K-000/01

File Segment: EPI

Manual Codes (EPI/S-X): U11-D; V04-A09; V04-B01; V04-M05; X25-S